

BUK9620-100B

N-channel TrenchMOS logic level FET

Rev. 02 — 6 May 2009

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC-Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

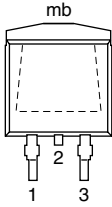
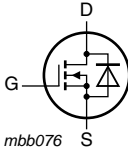
1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	100	V
I_D	drain current	$V_{GS} = 5\text{ V}; T_{mb} = 25\text{ °C};$ see Figure 1 ; see Figure 3	-	-	63	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ see Figure 2	-	-	203	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A};$ $T_j = 25\text{ °C};$ see Figure 11 ; see Figure 12	-	16.4	22.3	mΩ
		$V_{GS} = 5\text{ V}; I_D = 25\text{ A};$ $T_j = 25\text{ °C};$ see Figure 12 ; see Figure 11	-	16.2	20	mΩ
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 63\text{ A}; V_{sup} \leq 100\text{ V};$ $R_{GS} = 50\text{ }\Omega; V_{GS} = 5\text{ V};$ $T_{j(init)} = 25\text{ °C};$ unclamped	-	-	222	mJ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>SOT404 (D2PAK)</p>	 <p>mbb076</p>
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

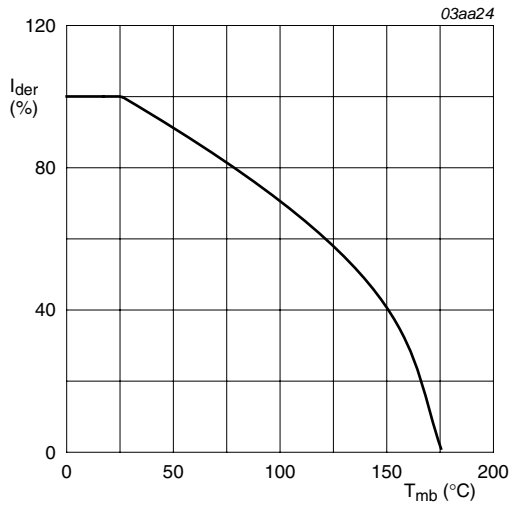
Type number	Package		Version
	Name	Description	
BUK9620-100B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

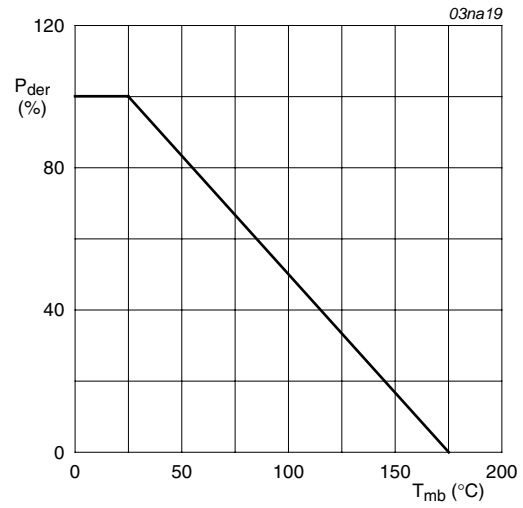
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-15	15	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 5\text{ V}$; see Figure 1 ; see Figure 3	-	63	A
		$T_{mb} = 100\text{ °C}$; $V_{GS} = 5\text{ V}$; see Figure 1	-	45	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}$; $t_p \leq 10\text{ }\mu\text{s}$; pulsed; see Figure 3	-	253	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	203	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	63	A
I_{SM}	peak source current	$t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$	-	253	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 63\text{ A}$; $V_{SUP} \leq 100\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 5\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped	-	222	mJ



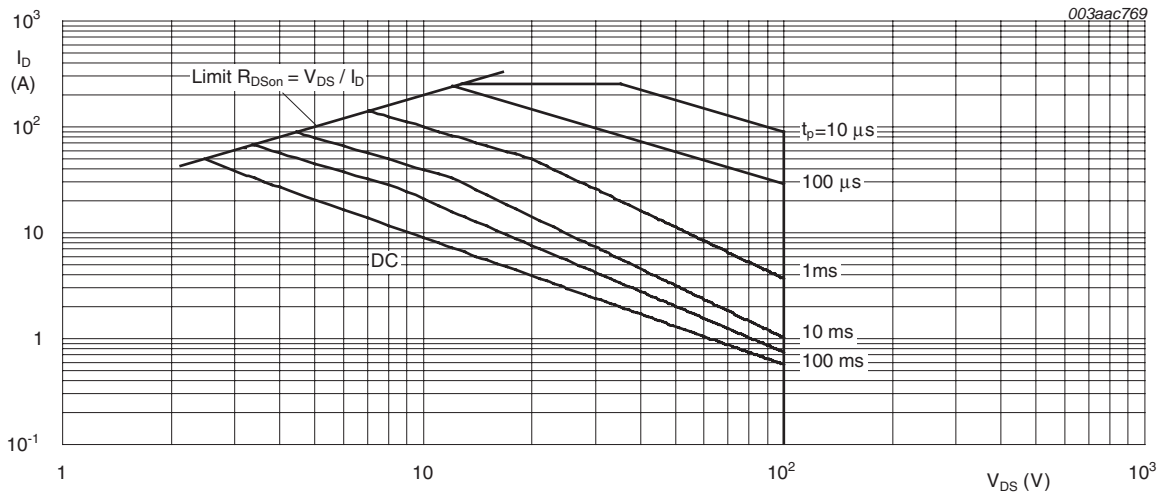
$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25^\circ\text{C}; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.75	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on printed circuit board; minimum footprint; SOT404 package	-	50	-	K/W

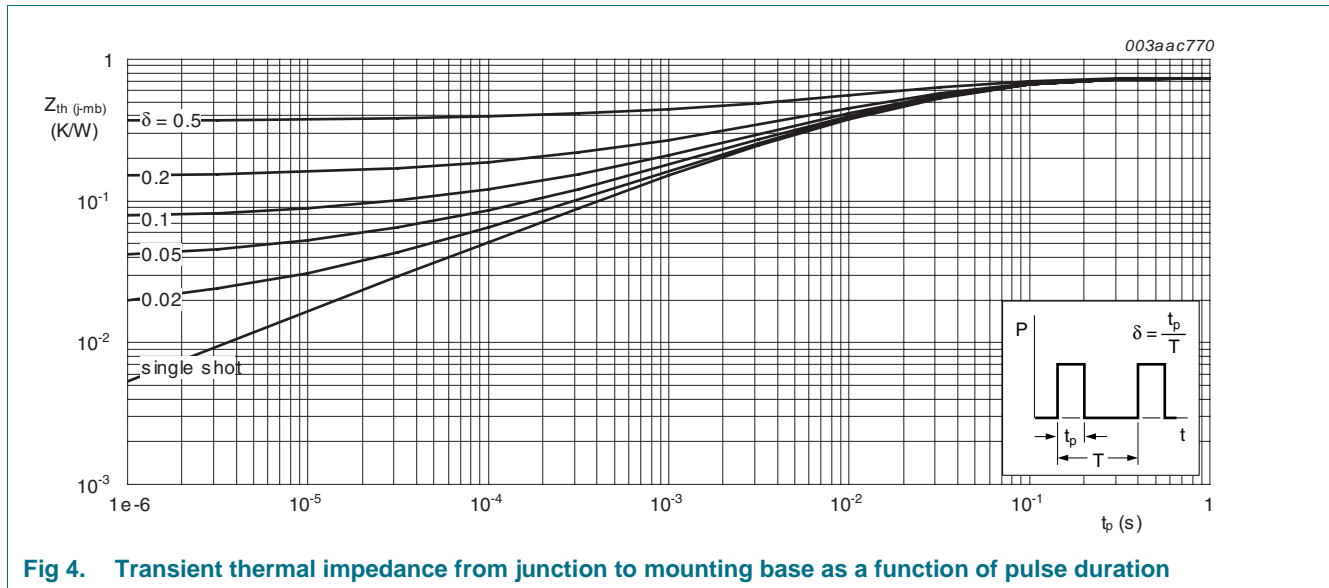


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

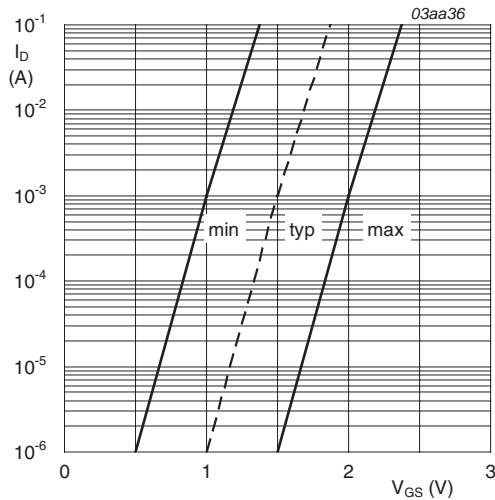
6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	100	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 10	1	1.58	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 10	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 10	-	-	2.3	V
I_{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.05	1	μA
I_{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 11 ; see Figure 12	-	16.4	22.3	m Ω
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 11 ; see Figure 12	-	15.6	18.5	m Ω
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 12 ; see Figure 11	-	-	50	m Ω
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 12 ; see Figure 11	-	16.2	20	m Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 14 ; see Figure 15	-	53.4	-	nC
Q_{GS}	gate-source charge		-	9.5	-	nC
Q_{GD}	gate-drain charge		-	21.2	-	nC
C_{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 16	-	4300	5657	pF
C_{oss}	output capacitance		-	340	411	pF
C_{rss}	reverse transfer capacitance		-	150	201	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \text{ }^\circ\Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 10 \text{ }^\circ\Omega; T_j = 25 \text{ }^\circ\text{C}$	-	45	-	ns
t_r	rise time		-	116	-	ns
$t_{d(off)}$	turn-off delay time		-	173	-	ns
t_f	fall time		-	77	-	ns
L_D	internal drain inductance	from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ }^\circ\text{C}$	-	4.5	-	nH
		from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ }^\circ\text{C}$	-	2.5	-	nH
L_S	internal source inductance	from source lead to source bond pad; $T_j = 25 \text{ }^\circ\text{C}$	-	7.5	-	nH

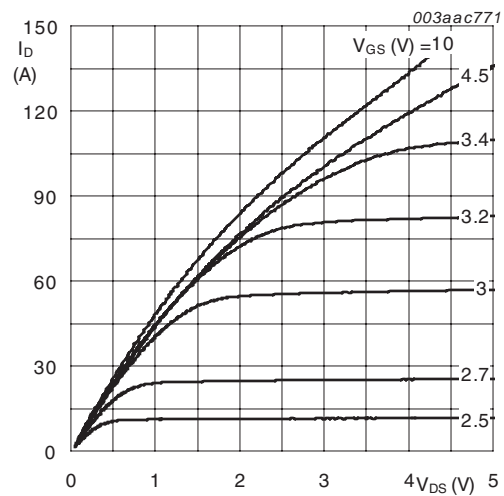
Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; see Figure 13	-	0.86	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$;	-	80	-	ns
Q_r	recovered charge	$V_{DS} = 30\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$	-	272	-	nC



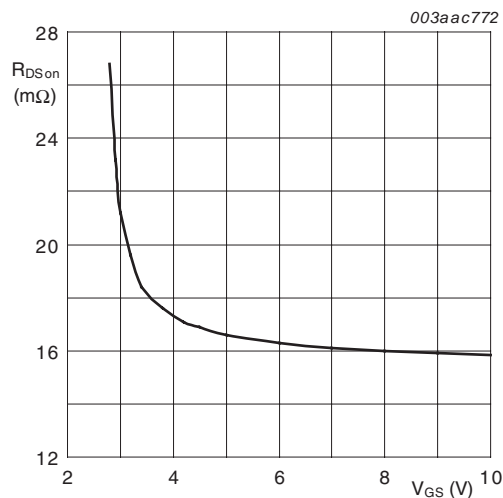
$T_j = 25\text{ }^\circ\text{C}$; $V_{DS} = V_{GS}$

Fig 5. Sub-threshold drain current as a function of gate-source voltage



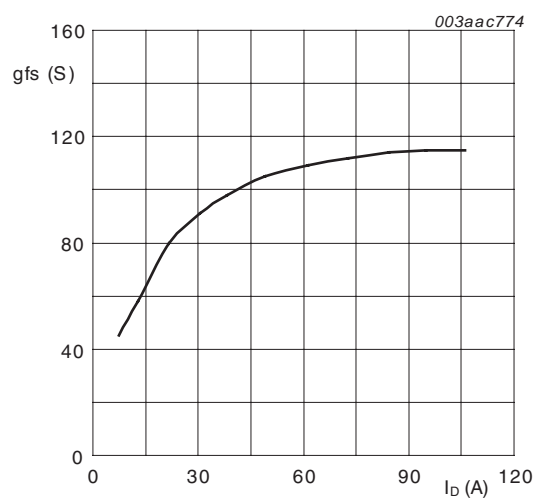
$T_j = 25\text{ }^\circ\text{C}$; $t_p = 300\mu\text{s}$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



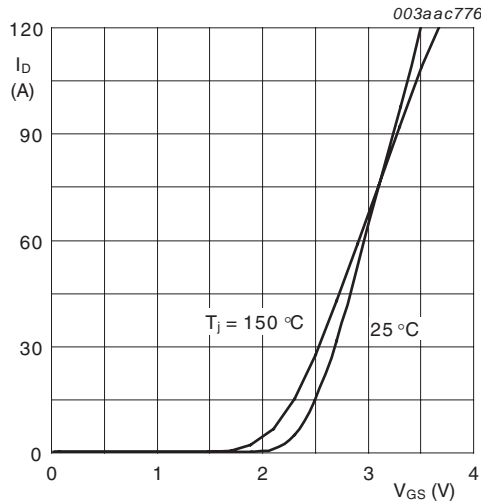
$T_j = 25\text{ }^\circ\text{C}$; $I_D = 25\text{ A}$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values.



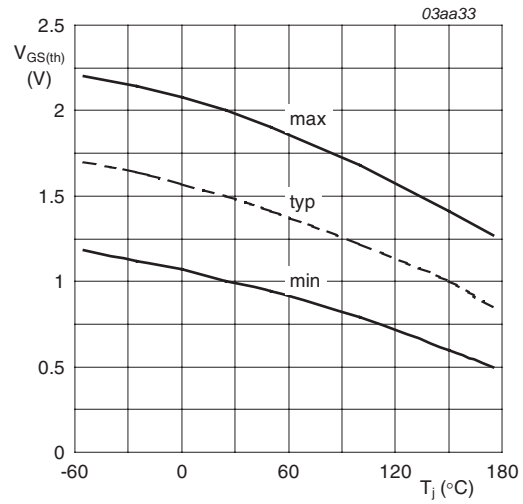
$T_j = 25\text{ }^\circ\text{C}$; $V_{DS} = 25\text{ V}$

Fig 8. Forward transconductance as a function of drain current; typical values.



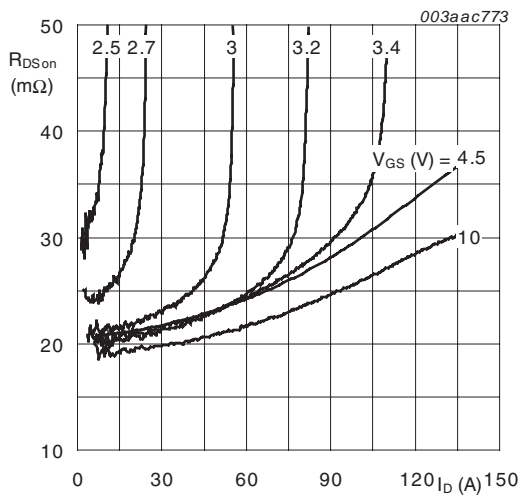
$$V_{DS} = 25V$$

Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



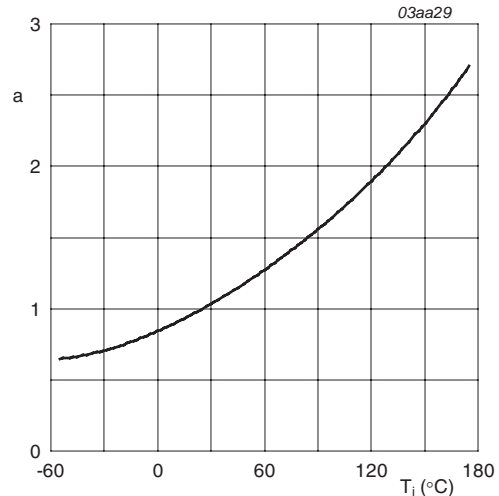
$$I_D = 1 mA; V_{DS} = V_{GS}$$

Fig 10. Gate-source threshold voltage as a function of junction temperature



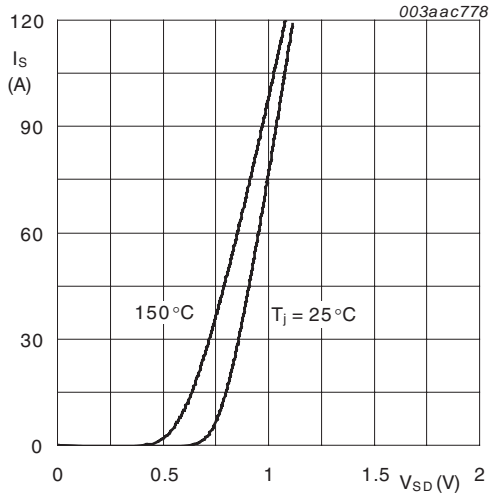
$$T_j = 25^\circ C$$

Fig 11. Drain-source on-state resistance as a function of drain current; typical values.



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



$V_{GS} = 0V$

Fig 13. Source current as a function of source drain voltage; typical values.

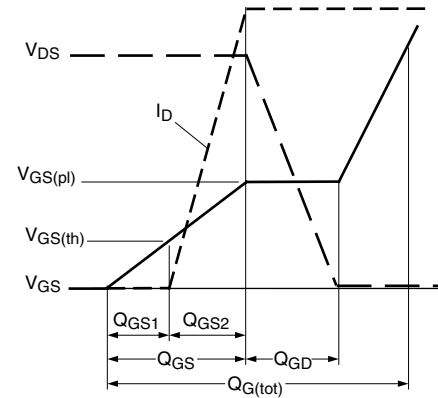
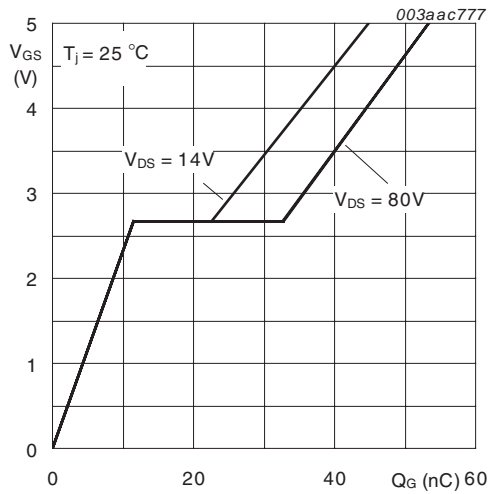
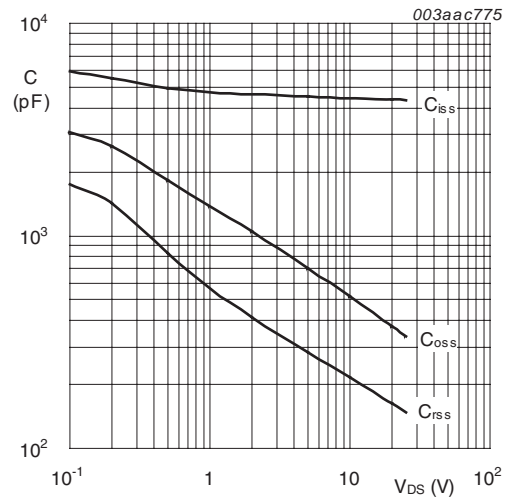


Fig 14. Gate charge waveform definitions



$T_j = 25^\circ C; I_D = 25A$

Fig 15. Gate-source voltage as a function of turn-on gate charge; typical values.



$V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404

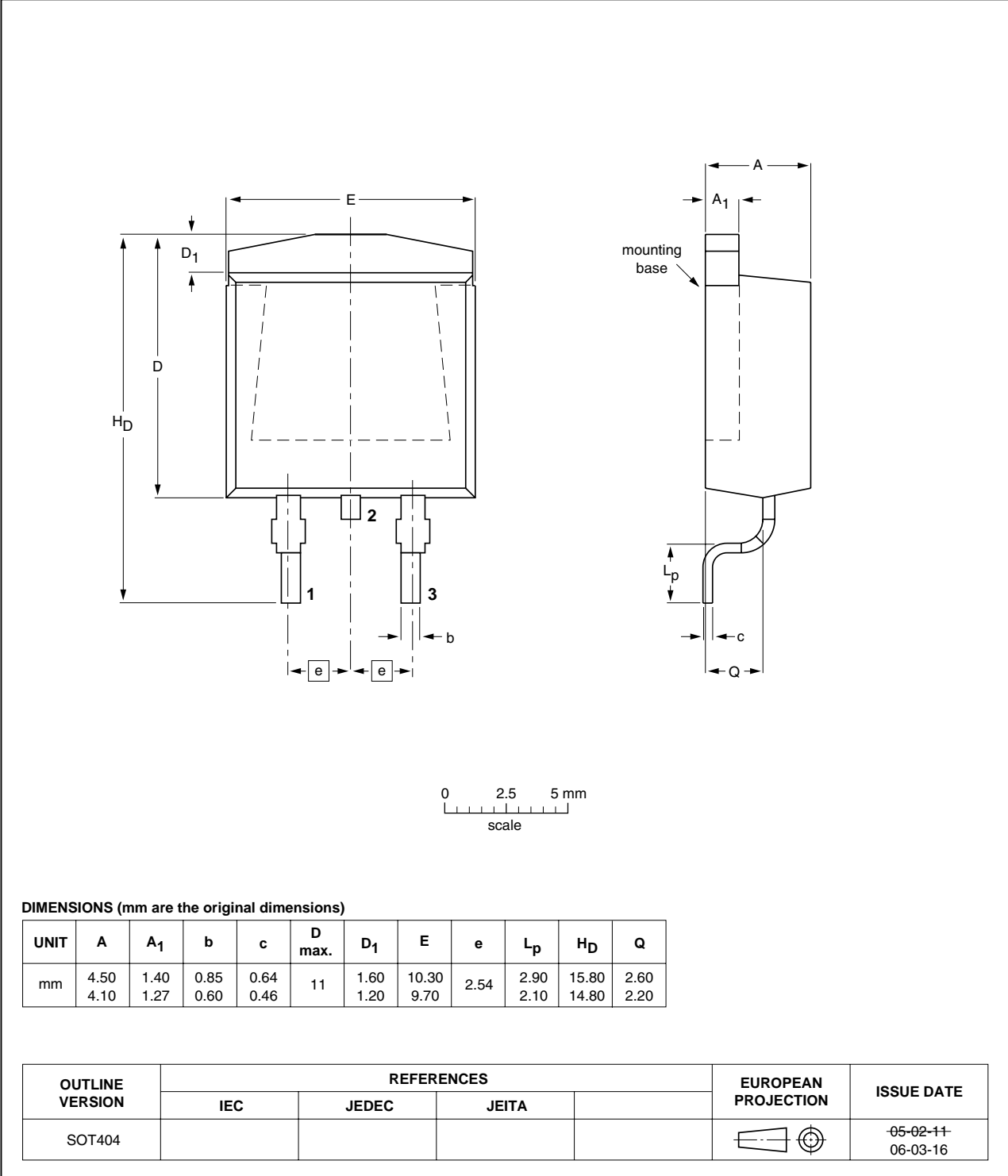


Fig 17. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9620-100B_2	20090506	Product data sheet	-	BUK9620-100B_1
Modifications:	• Data sheet status changed from 'Objective' to 'Product'.			
BUK9620-100B_1	20090323	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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